

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant	:	Raina, et al.
App. No.	:	Unknown
Filed	:	Herewith
For	:	NITROGEN AND PHOSPHORUS DOPED AMORPHOUS SILICON AS RESISTOR FOR FIELD EMISSION DISPLAY DEVICE BASEPLATE
Examiner	:	Roy Sikha
Group Art Unit	:	2879

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

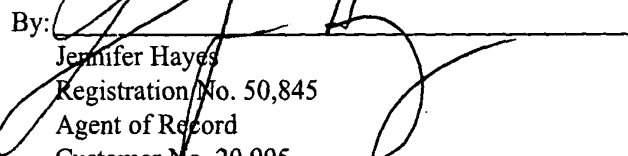
Enclosed is form PTO-1449 listing seventeen (17) references. These references are of record in related U.S. Patent Application 09/388,697, filed September 2, 1999. The present application claims priority from this related application under 35 U.S.C. § 120. Accordingly, pursuant to 37 C.F.R. § 198(d), copies of these references are not included. This Information Disclosure Statement is being filed within three months of the filing date of this application, and no fee is required in accordance with 37 C.F.R. § 1.97(b)(1), (b)(2), or (b)(4).

Identification herein is not an admission that any of the foregoing are prior art to the above-captioned application.

Respectfully submitted,

KNOBBE, MARTENS, OLSON & BEAR, LLP

Dated: August 19, 2003

By: 
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FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICANT (USE SEVERAL SHEETS IF NECESSARY)	ATTY. DOCKET NO. MICRON.111C1	APPLICATION NO. Unknown
	APPLICANT Raina, et al.	
	FILING DATE Herewith	GROUP 2879

U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
	1	4,084,986	04/18/78	Aoki, et al.	148	1.5	
	2	4,940,916	07-1990	Borel, et al.	313	306	
	3	5,585,301	12-1996	Lee, et al.	313	306	
	4	5,714,415	02/03/98	Oguro	438	486	
	5	5,789,851	08-1998	Turlot, et al.	313	309	
	6	5,866,930	02-1999	Saida, et al.	257	316	
	7	5,902,650	05-1999	Feng, et al.	427	578	
	8	6,015,323	01/18/00	Moradi, et al.	445	24	
	9	6,019,657	02-2000	Chakvorty, et al.	445	24	
	10	6,064,149	05/16/00	Raina	313	497	
	11	6,181,308	01/30/01	Cathey, et al.	345	75.2	
	12	6,190,929	02-2001	Wang, et al.	438	20	
	13	6,211,608	04-2001	Raina, et al.	313	309	

FOREIGN PATENT DOCUMENTS								
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	14	JP 04168763 A	06-1992	Japan	H01L	27/04		

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)	
	15	Young-Chang Joo, et al. 1996. Electromigration in single-crystal aluminum lines pre-damaged by nanoindentation, <i>Materials Research Society Symp. Proc.</i> , 428:225-230.
	16	Atsushi Masuda, et al. 15 May 1997. Nitrogen-doping effects on electrical, optical, and structural properties in hydrogenated amorphous silicon. American Institute of Physics. <i>J. Appl. Phys.</i> , 81(10):6729-6737.
	17	C-K. Hu, et al. 1993. Electromigration damage in fine A1 alloy lines due to interfacial diffusion. <i>Materials Research Society Symp. Proc.</i> , 309:111-120.

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070703

EXAMINER	DATE CONSIDERED
*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.	